

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows.

1. (Currently Amended) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:  
  
growing nitride crystals of a hexagonal system on a ~~substrate-surface~~ of a substrate; ~~and~~  
  
cutting said substrate along two directions that form a 120 degree angle;  
  
forming a light-emitting section on a central section of the nitride semiconductor chip;  
  
and  
  
forming an electrode at opposing ends of a planar surface of the nitride semiconductor chip.
2. (Currently Amended) A method according to claim 1, further comprising, between said growing step and said cutting step, the step of grinding a ~~the~~ back surface of said substrate.
3. (Currently Amended) A method according to claim 2, further comprising the step of:  
  
making scratches on one of a the-front surface and a ~~the-front surface and a~~ [[or ]] back surface of said substrate,  
  
between said grinding step and said cutting step, wherein  
  
said cutting step is performed by cutting said substrate along [[the ]] directions of said scratches.
4. (Currently Amended) A method according to claim 1, wherein said semiconductor chip has a ~~planer~~ planar shape of a rhombus.
5. (Original) A method according to claim 1, wherein said substrate is sapphire.
6. (Original) A method according to claim 1, wherein said nitride crystals include GaN.

7. (Withdrawn) A nitride semiconductor chip, comprising:
  - a substrate; and
  - nitride crystals of a hexagonal system and formed on said substrate; wherein  
the planer shape of said semiconductor chip is a rhombus having an interior angle  
of 120 degrees.
8. (Withdrawn) A semiconductor chip according to claim 7, further comprising:
  - a light emitting section formed on the central section of said rhombus of the planer shape  
of said semiconductor chip; and
  - electrode sections formed at both ends of said rhombus to pinch said light emitting  
section.
9. (Withdrawn) A semiconductor chip according to claim 8, wherein the planer shape of said  
electrode sections is triangular.
10. (Withdrawn) A semiconductor chip according to claim 7, wherein said substrate is a  
sapphire.
11. (Withdrawn) A semiconductor chip according to claim 7, wherein said nitride crystals  
include a GaN.
12. (New) A method for manufacturing a nitride semiconductor chip, said method comprising  
the steps of:
  - growing nitride crystals of a hexagonal system on a surface of a substrate;
  - grinding a back surface of said substrate; and
  - cutting said substrate along two directions that form a 120 degree angle.
13. (New) A method according to claim 12, further comprising the step of:
  - making scratches on one of a front and a back surface of said substrate, between said  
grinding step and said cutting step, wherein  
said cutting step is performed by cutting said substrate along directions of said scratches.

14. (New) A method according to claim 12, wherein said semiconductor chip has a planar shape of a rhombus.
15. (New) A method according to claim 12, wherein said substrate is sapphire.
16. (New) A method according to claim 12, wherein said nitride crystals include GaN.